

Switch-mode Power Rectifier

60 V, 30 A

MBR30L60CTG, MBRF30L60CTG

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capability
- 30 A Total (15 A Per Diode Leg)
- Guard-Ring for Stress Protection
- These Devices are Pb-Free and are RoHS Compliant

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics:

- Case: Epoxy, Molded
- Epoxy Meets UL 94 V-0 @ 0.125 in
- Weight (Approximately): 1.9 Grams (TO-220 & TO-220FP)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

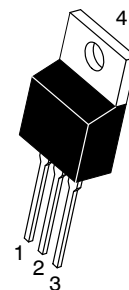
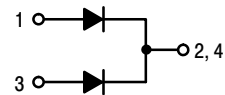


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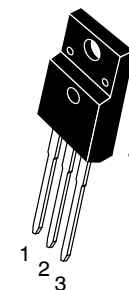
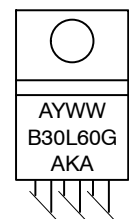
SCHOTTKY BARRIER RECTIFIER

30 AMPERES, 60 VOLTS

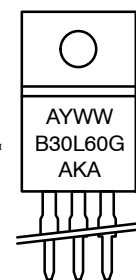


TO-220
CASE 221A
STYLE 6

MARKING DIAGRAMS



TO-220 FULLPAK™
CASE 221D



- A = Assembly Location
- Y = Year
- WW = Work Week
- B30L60 = Device Code
- G = Pb-Free Device
- AKA = Polarity Designator

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

MBR30L60CTG, MBRF30L60CTG

MAXIMUM RATINGS (Per Diode Leg)

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	60	V
Average Rectified Forward Current (Per Leg) MBR30L60CTG (Rated V_R) $T_C = 133^\circ\text{C}$ (Per Device) MBRF30L60CTG (Rated V_R) $T_C = 108^\circ\text{C}$ (Per Device)	$I_{F(AV)}$	15 30	A
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)	I_{FSM}	240	A
Operating Junction Temperature (Note 1)	T_J	-55 to +150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-65 to +175	$^\circ\text{C}$
ESD Ratings: Machine Model = C Human Body Model = 3B		> 400 > 8000	V

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. The heat generated must be less than the thermal conductivity from Junction-to-Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Maximum Thermal Resistance MBR30L60CTG Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	2.1 70	$^\circ\text{C/W}$
MBRF30L60CTG Junction-to-Case Junction-to-Ambient	$R_{\theta JC}$ $R_{\theta JA}$	5.0 75	

ELECTRICAL CHARACTERISTICS (Per Diode Leg)

Characteristic	Symbol	Typ	Max	Unit
Maximum Instantaneous Forward Voltage (Note 2) ($I_F = 15\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 15\text{ A}$, $T_C = 125^\circ\text{C}$) ($I_F = 30\text{ A}$, $T_C = 25^\circ\text{C}$) ($I_F = 30\text{ A}$, $T_C = 125^\circ\text{C}$)	V_F	0.57 0.53 0.75 0.70	0.62 0.57 0.81 0.73	V
Maximum Instantaneous Reverse Current (Note 2) (Rated DC Voltage, $T_C = 25^\circ\text{C}$) (Rated DC Voltage, $T_C = 125^\circ\text{C}$)	i_R	137 62	350 110	μA mA

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

2. Pulse Test: Pulse Width = 300 μs , Duty Cycle $\leq 2.0\%$.

DEVICE ORDERING INFORMATION

Device Order Number	Package Type	Shipping
MBR30L60CTG	TO-220 (Pb-Free)	50 Units / Rail
MBRF30L60CTG	TO-220FP (Pb-Free)	50 Units / Rail

MBR30L60CTG, MBRF30L60CTG

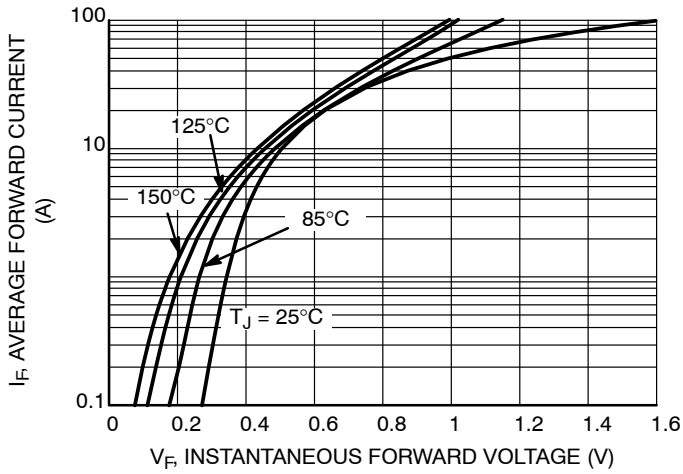


Figure 1. Typical Forward Voltage

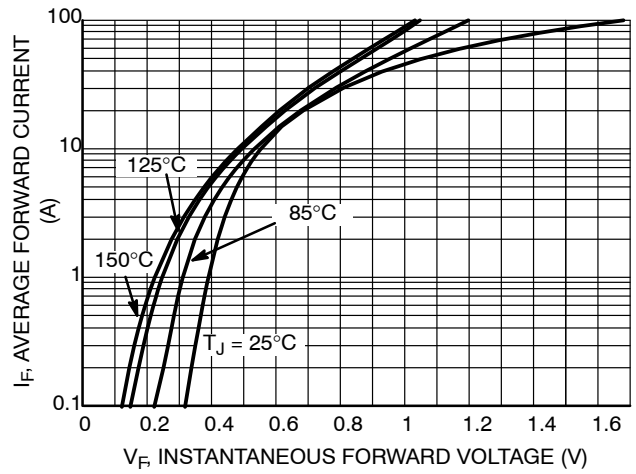


Figure 2. Maximum Forward Voltage

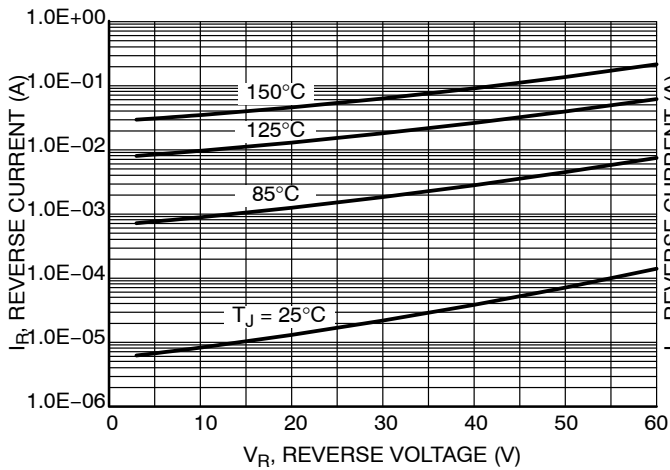


Figure 3. Typical Reverse Current

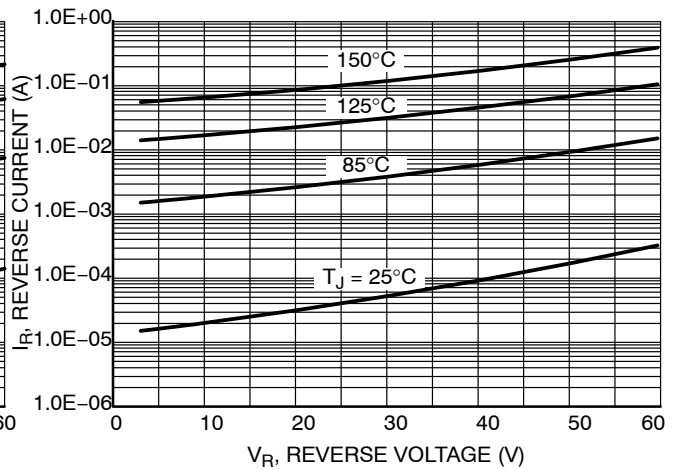


Figure 4. Maximum Reverse Current

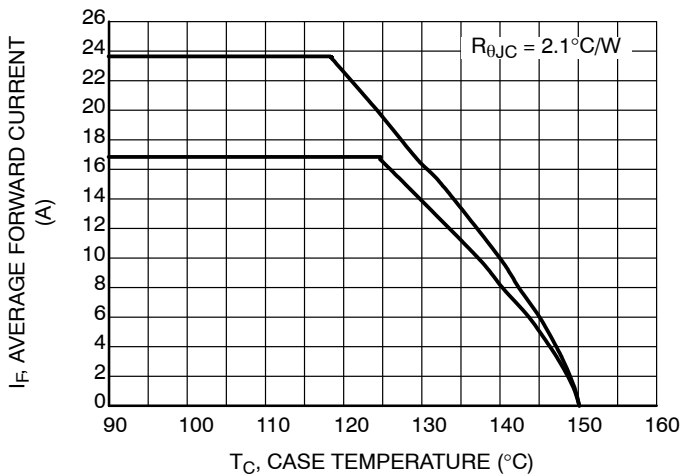


Figure 5. Current Derating, Case per Leg
MBR30L60CT

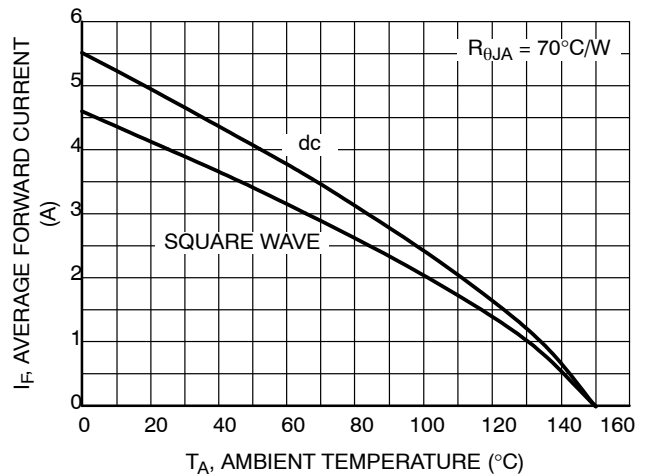


Figure 6. Current Derating, Ambient per Leg
MBR30L60CT

MBR30L60CTG, MBRF30L60CTG

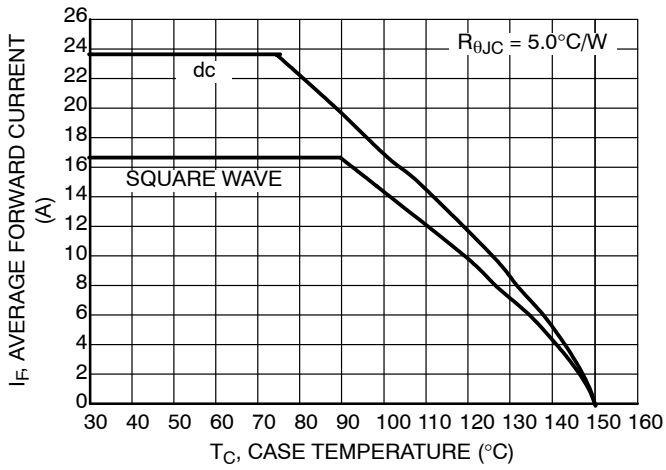


Figure 7. Current Derating, Case per Leg MBRF30L60CT

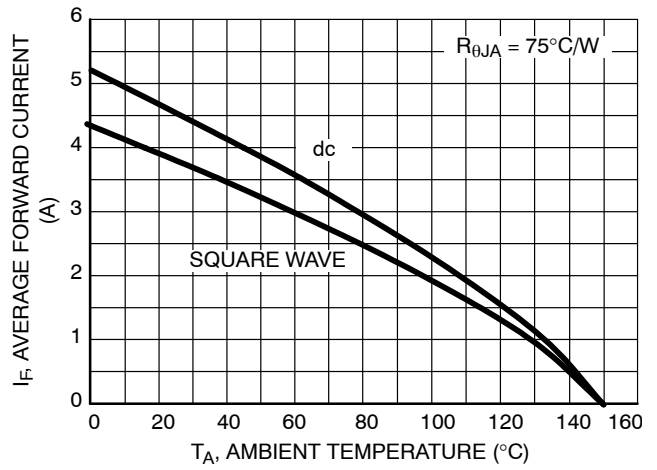


Figure 8. Current Derating, Ambient per Leg MBRF30L60CT

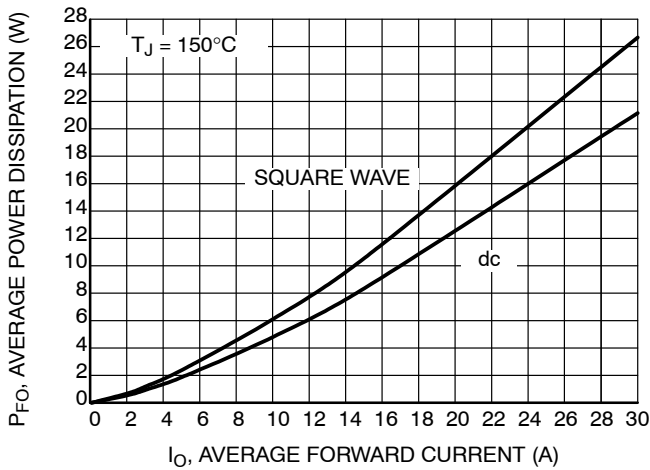


Figure 9. Forward Power Dissipation

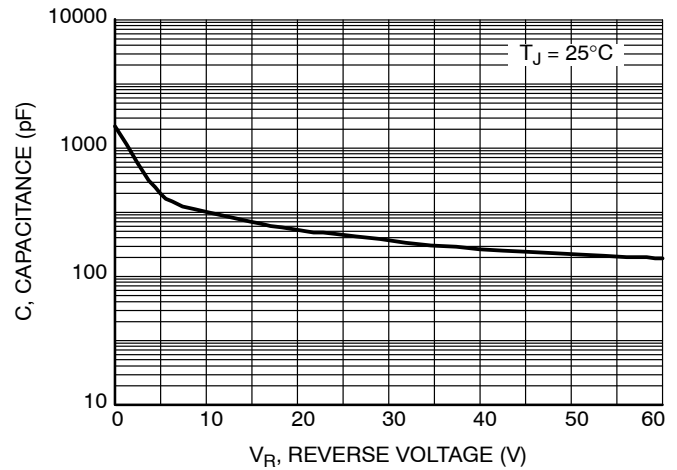


Figure 10. Capacitance

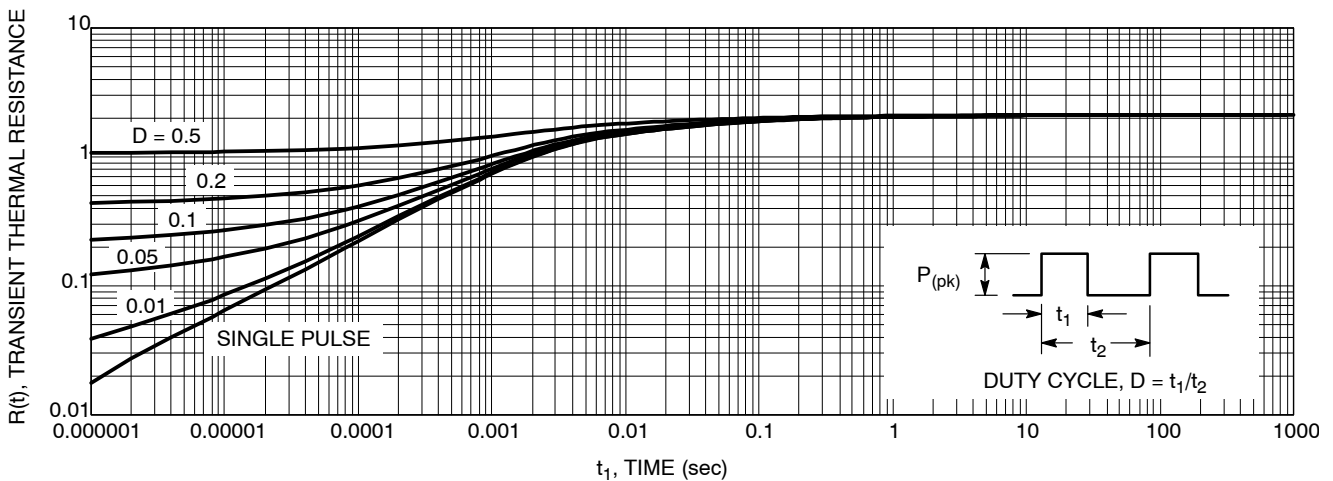


Figure 11. Thermal Response Junction-to-Case, per Leg for MBR30L60CT

MBR30L60CTG, MBRF30L60CTG

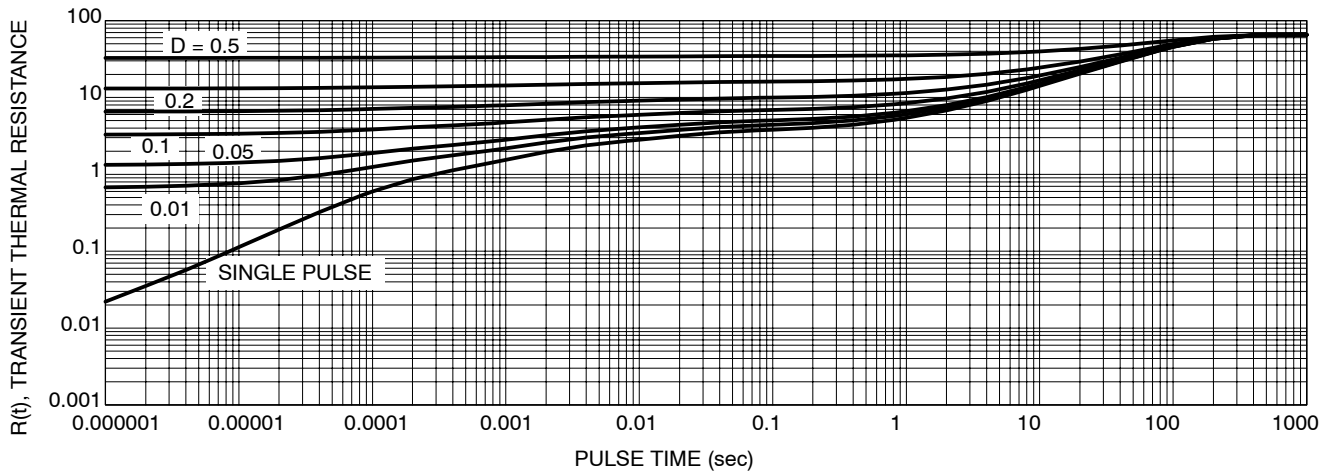


Figure 12. Thermal Response Junction-to-Ambient, per Leg for MBR30L60CT

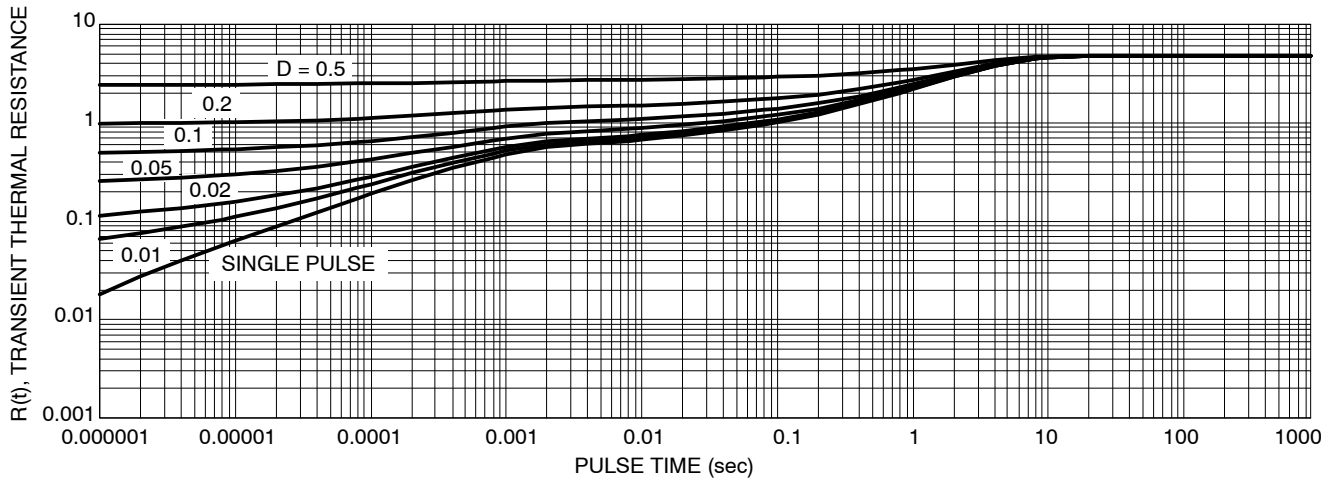


Figure 13. Thermal Response Junction-to-Case, per Leg for MBRF30L60CT

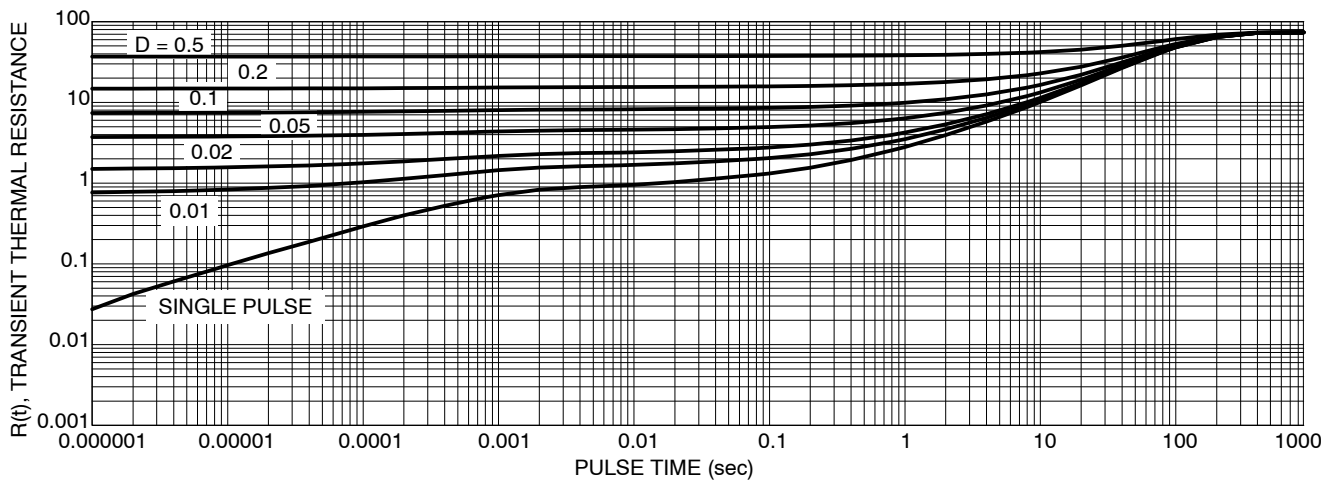
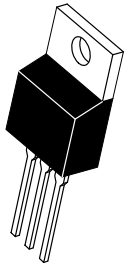


Figure 14. Thermal Response Junction-to-Ambient, per Leg for MBRF30L60CT

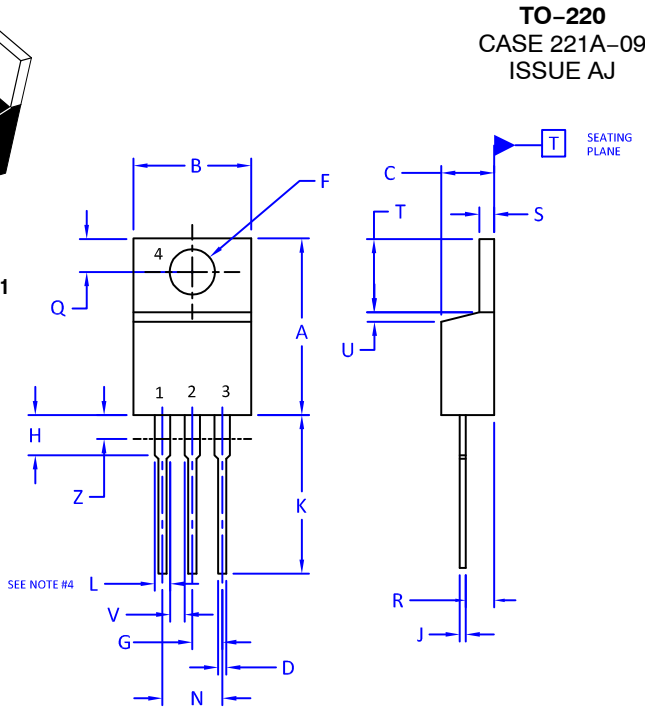
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®



SCALE 1:1



TO-220
CASE 221A-09
ISSUE AJ

DATE 05 NOV 2019

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 2009.
2. CONTROLLING DIMENSION: INCHES
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.
4. MAX WIDTH FOR F102 DEVICE = 1.35MM

DIM	INCHES		MILLIMETERS	
	MIN.	MAX.	MIN.	MAX.
A	0.570	0.620	14.48	15.75
B	0.380	0.415	9.66	10.53
C	0.160	0.190	4.07	4.83
D	0.025	0.038	0.64	0.96
F	0.142	0.161	3.60	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.161	2.80	4.10
J	0.014	0.024	0.36	0.61
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.41
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 1:

- PIN 1. BASE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 2:

- PIN 1. BASE
- 2. EMITTER
- 3. COLLECTOR
- 4. EMITTER

STYLE 3:

- PIN 1. CATHODE
- 2. ANODE
- 3. GATE
- 4. ANODE

STYLE 4:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. MAIN TERMINAL 2

STYLE 5:

- PIN 1. GATE
- 2. DRAIN
- 3. SOURCE
- 4. DRAIN

STYLE 6:

- PIN 1. ANODE
- 2. CATHODE
- 3. ANODE
- 4. CATHODE

STYLE 7:

- PIN 1. CATHODE
- 2. ANODE
- 3. CATHODE
- 4. ANODE

STYLE 8:

- PIN 1. CATHODE
- 2. ANODE
- 3. EXTERNAL TRIP/DELAY
- 4. ANODE

STYLE 9:

- PIN 1. GATE
- 2. COLLECTOR
- 3. EMITTER
- 4. COLLECTOR

STYLE 10:

- PIN 1. GATE
- 2. SOURCE
- 3. DRAIN
- 4. SOURCE

STYLE 11:

- PIN 1. DRAIN
- 2. SOURCE
- 3. GATE
- 4. SOURCE

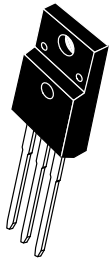
STYLE 12:

- PIN 1. MAIN TERMINAL 1
- 2. MAIN TERMINAL 2
- 3. GATE
- 4. NOT CONNECTED

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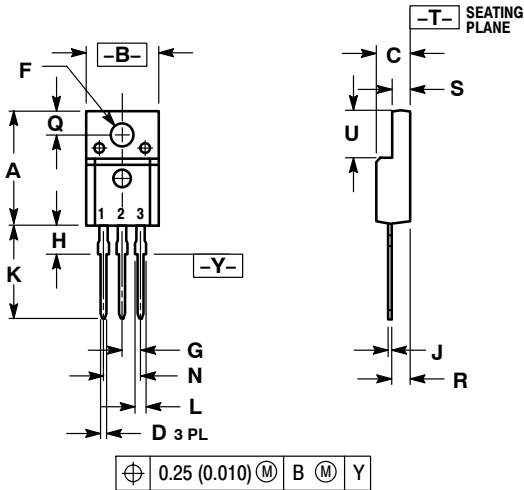
MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



SCALE 1:1

TO-220 FULLPAK CASE 221D-03 ISSUE K

DATE 27 FEB 2009



- NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 2. CONTROLLING DIMENSION: INCH
 3. 221D-01 THRU 221D-02 OBSOLETE, NEW STANDARD 221D-03.

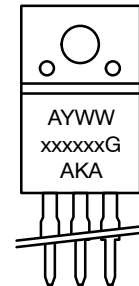
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

MARKING DIAGRAMS

- | | | |
|--|---|--|
| <p>STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE</p> | <p>STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. EMITTER</p> | <p>STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE</p> |
| <p>STYLE 4:
PIN 1. CATHODE
2. ANODE
3. CATHODE</p> | <p>STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE</p> | <p>STYLE 6:
PIN 1. MT 1
2. MT 2
3. GATE</p> |



Bipolar



Rectifier

- | | |
|-------------------------------|---------------------------|
| xxxxxx = Specific Device Code | A = Assembly Location |
| G = Pb-Free Package | Y = Year |
| A = Assembly Location | WW = Work Week |
| Y = Year | xxxxxx = Device Code |
| WW = Work Week | G = Pb-Free Package |
| | AKA = Polarity Designator |

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